



SEMITOP®E2

Sixpack Open Emitter

SK100GD12T7ETE2

Features*

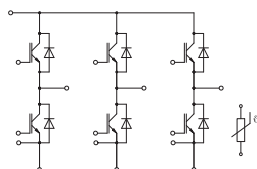
- Optimized design for superior thermal performance
- Low inductive design
- Press-Fit contact technology
- 1200V Generation 7 IGBT (T7)
- Robust and soft switching CAL4F diode technology
- Integrated NTC temperature sensor
- UL recognized file no. E 63 532

Typical Applications

- Motor drives
- Servo drives
- Air conditioning
- Auxiliary Inverters
- UPS

Remarks

- Recommended $T_{j,op} = -40 \dots +150 \text{ }^{\circ}\text{C}$
- $T_{j,op} > 150 \text{ }^{\circ}\text{C}$ during overload (details on AN19-002)



GD-ET

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
Inverter - IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _C	λ _{paste} =0.8 W/(mK)	T _s = 70 °C	94	A
	T _j = 175 °C	T _s = 100 °C	75	A
I _C	λ _{paste} =2.5 W/(mK)	T _s = 70 °C	124	A
	T _j = 175 °C	T _s = 100 °C	101	A
I _{Cnom}			100	A
I _{CRM}			200	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 800 V V _{GE} ≤ 15 V V _{CES} ≤ 1200 V	T _j = 175 °C	7	μs
T _j			-40 ... 175	°C
Inverse - Diode				
V _{RRM}	T _j = 25 °C		1200	V
I _F	λ _{paste} =0.8 W/(mK)	T _s = 70 °C	73	A
	T _j = 175 °C	T _s = 100 °C	58	A
I _F	λ _{paste} =2.5 W/(mK)	T _s = 70 °C	96	A
	T _j = 175 °C	T _s = 100 °C	77	A
I _{FRM}			200	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 150 °C		550	A
T _j			-40 ... 175	°C
Module				
I _{t(RMS)}	, ΔT _{terminal} at PCB joint = 30 K, per pin		30	A
T _{stg}	module without TIM		-40 ... 125	°C
V _{isol}	AC, sinusoidal, t = 1 min		2500	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverter - IGBT						
V _{CE(sat)}	I _C = 100 A	T _j = 25 °C		1.55	1.70	V
	V _{GE} = 15 V	T _j = 150 °C		1.70	1.88	V
	chiplevel	T _j = 175 °C		1.77	1.92	V
V _{CE0}		T _j = 25 °C		1.00	1.05	V
	chiplevel	T _j = 150 °C		0.80	0.85	V
		T _j = 175 °C		0.75	0.80	V
r _{CE}		T _j = 25 °C		5.5	6.5	mΩ
	V _{GE} = 15 V	T _j = 150 °C		9.0	10	mΩ
	chiplevel	T _j = 175 °C		10	11	mΩ
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 2.05 mA		5.15	5.8	6.45	V
I _{CES}	V _{GE} = 0 V, V _{CE} = 1200 V, T _j = 25 °C				1	mA
C _{ies}	V _{CE} = 25 V V _{GE} = 0 V	f = 1 MHz		20.00		nF
C _{oes}		f = 1 MHz		0.25		nF
C _{res}		f = 1 MHz		0.07		nF
Q _G	V _{GE} = -15V...+15V			1613		nC
R _{Gint}	T _j = 25 °C			1.5		Ω



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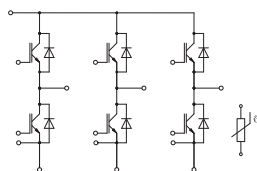
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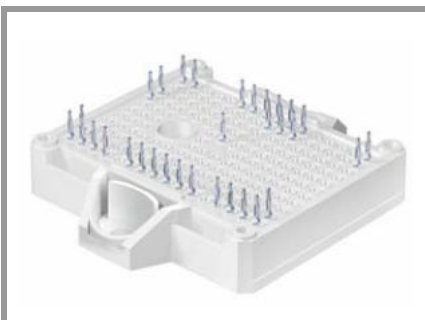


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Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
Inverter - IGBT					
$t_{d(on)}$	$T_j = 25 \text{ }^{\circ}\text{C}$ $T_j = 150 \text{ }^{\circ}\text{C}$ $T_j = 175 \text{ }^{\circ}\text{C}$		117		ns
			133		ns
			137		ns
t_r	$T_j = 25 \text{ }^{\circ}\text{C}$ $T_j = 150 \text{ }^{\circ}\text{C}$ $T_j = 175 \text{ }^{\circ}\text{C}$		27		ns
			33		ns
			35		ns
E_{on}	$V_{CC} = 600 \text{ V}$ $I_C = 100 \text{ A}$ $R_{G on} = 1.8 \text{ } \Omega$ $R_{G off} = 1.8 \text{ } \Omega$ $V_{GE} = +15/-15 \text{ V}$ $T_j = 25 \text{ }^{\circ}\text{C}$ $T_j = 150 \text{ }^{\circ}\text{C}$ $T_j = 175 \text{ }^{\circ}\text{C}$		4.98		mJ
			8.65		mJ
			9.57		mJ
$t_{d(off)}$	$(T_j = 150 \text{ }^{\circ}\text{C})$ $di/dt_{on} = 3200 \text{ A}/\mu\text{s}$ $di/dt_{off} = 940 \text{ A}/\mu\text{s}$ $dv/dt = 3800 \text{ V}/\mu\text{s}$ $T_j = 25 \text{ }^{\circ}\text{C}$ $T_j = 150 \text{ }^{\circ}\text{C}$ $T_j = 175 \text{ }^{\circ}\text{C}$		243		ns
			323		ns
			342		ns
t_f	$T_j = 25 \text{ }^{\circ}\text{C}$ $T_j = 150 \text{ }^{\circ}\text{C}$ $T_j = 175 \text{ }^{\circ}\text{C}$		52		ns
			77		ns
			81		ns
E_{off}	$T_j = 25 \text{ }^{\circ}\text{C}$ $T_j = 150 \text{ }^{\circ}\text{C}$ $T_j = 175 \text{ }^{\circ}\text{C}$		6.16		mJ
			10.46		mJ
			11.53		mJ
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=0.8 \text{ W}/(\text{mK})$		0.61		K/W
$R_{th(j-s)}$	per IGBT, $\lambda_{paste}=2.5 \text{ W}/(\text{mK})$		0.39		K/W

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
Inverse - Diode					
$V_F = V_{EC}$	$I_F = 100 \text{ A}$ chiplevel $T_j = 25 \text{ }^{\circ}\text{C}$ $T_j = 150 \text{ }^{\circ}\text{C}$ $T_j = 175 \text{ }^{\circ}\text{C}$		2.20	2.52	V
			2.15	2.47	V
			2.00	2.31	V
V_{F0}	chiplevel $T_j = 25 \text{ }^{\circ}\text{C}$ $T_j = 150 \text{ }^{\circ}\text{C}$ $T_j = 175 \text{ }^{\circ}\text{C}$		1.30	1.50	V
			0.90	1.10	V
			0.82	0.98	V
r_F	chiplevel $T_j = 25 \text{ }^{\circ}\text{C}$ $T_j = 150 \text{ }^{\circ}\text{C}$ $T_j = 175 \text{ }^{\circ}\text{C}$		9.0	10	m Ω
			13	14	m Ω
			12	13	m Ω
I_{RRM}	$I_F = 100 \text{ A}$ $V_{GE} = +15/-15 \text{ V}$ $V_{CC} = 600 \text{ V}$ $(T_j = 150 \text{ }^{\circ}\text{C})$ $di/dt_{off} = 3500 \text{ A}/\mu\text{s}$ $T_j = 25 \text{ }^{\circ}\text{C}$ $T_j = 150 \text{ }^{\circ}\text{C}$ $T_j = 175 \text{ }^{\circ}\text{C}$		119		A
			166		A
			176		A
Q_{rr}	$T_j = 25 \text{ }^{\circ}\text{C}$ $T_j = 150 \text{ }^{\circ}\text{C}$ $T_j = 175 \text{ }^{\circ}\text{C}$		6.79		μC
			17.11		μC
			19.74		μC
E_{rr}	$T_j = 25 \text{ }^{\circ}\text{C}$ $T_j = 150 \text{ }^{\circ}\text{C}$ $T_j = 175 \text{ }^{\circ}\text{C}$		3.04		mJ
			7.89		mJ
			9.01		mJ
$R_{th(j-s)}$	per Diode, $\lambda_{paste}=0.8 \text{ W}/(\text{mK})$		0.74		K/W
$R_{th(j-s)}$	per Diode, $\lambda_{paste}=2.5 \text{ W}/(\text{mK})$		0.49		K/W
Module					
L_{CE}			40		nH
M_s	to heatsink	1.6		2.3	Nm
w			35		g

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Characteristics					
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Temperature Sensor					
R_{100}	$T_c=100^{\circ}\text{C}$ ($R_{25}=5\text{ k}\Omega$)		$493 \pm 5\%$		Ω
$B_{25/85}$	$R(T)=R_{25} \cdot \exp[B_{25/85} \cdot (1/T - 1/298)]$, $T[\text{K}]$		3420		K

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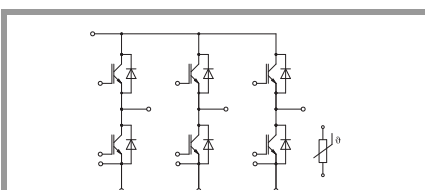
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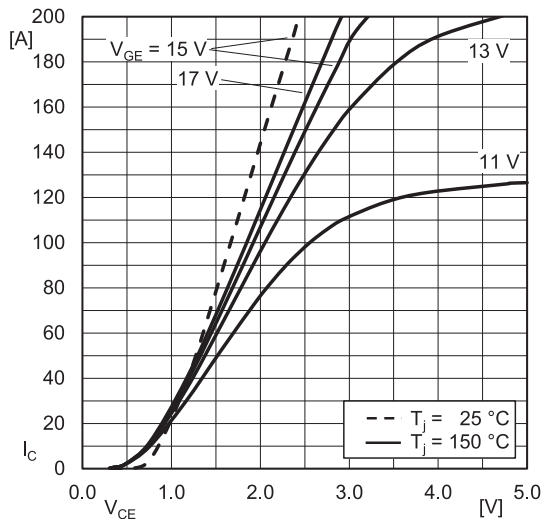


Fig. 1: Typ. IGBT output characteristic, incl. $R_{CC+EE'}$

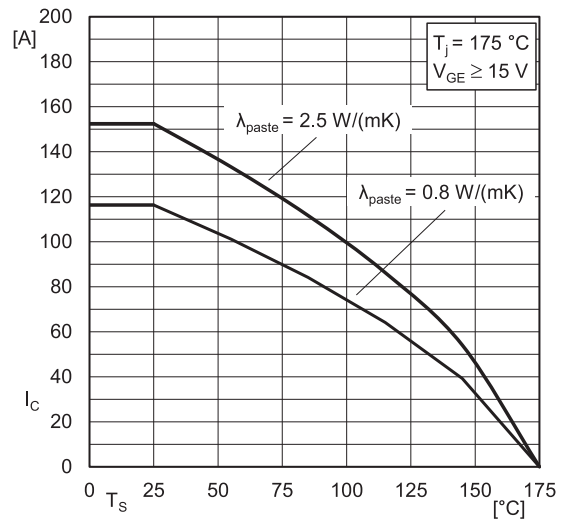


Fig. 2: IGBT rated current vs. temperature $I_C = f(T_s)$

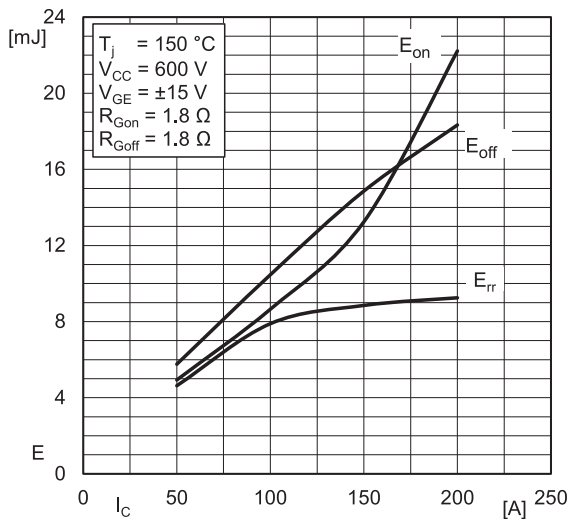


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

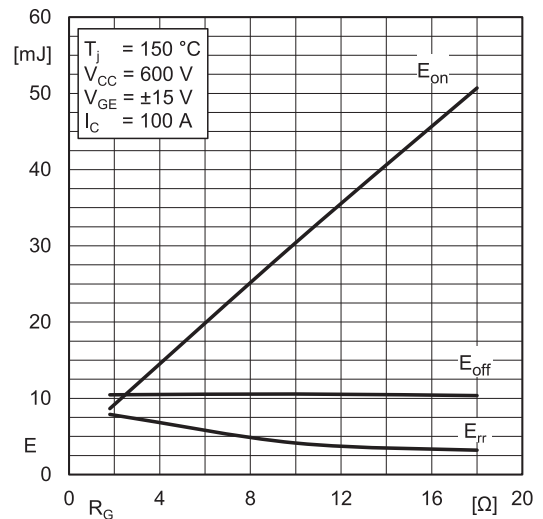


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

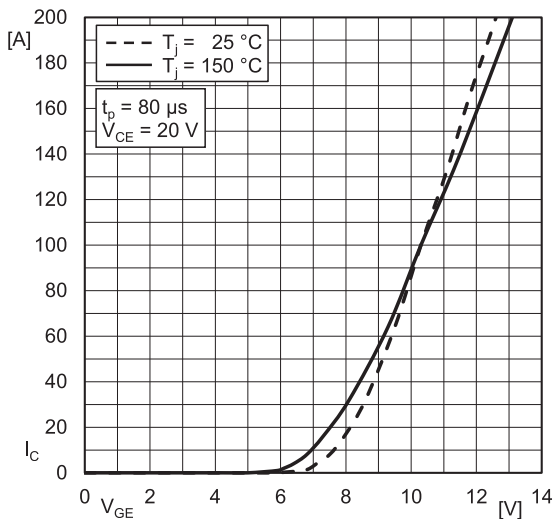


Fig. 5: Typ. IGBT transfer characteristic

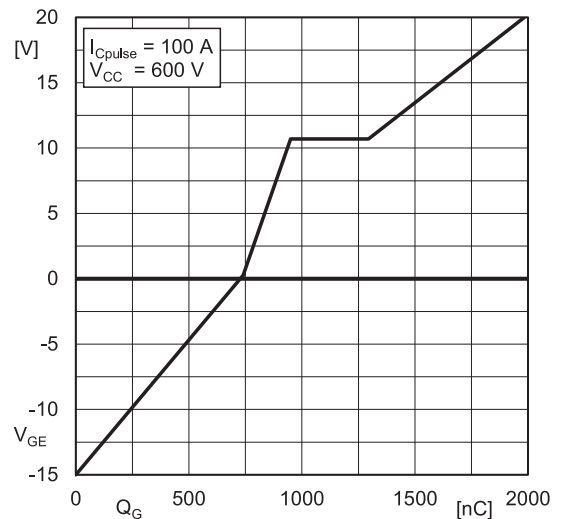


Fig. 6: Typ. IGBT gate charge characteristic

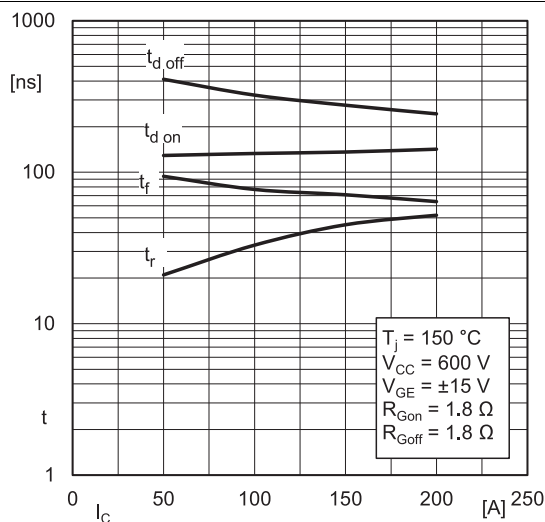


Fig. 7: Typ. switching times = $f(I_C)$

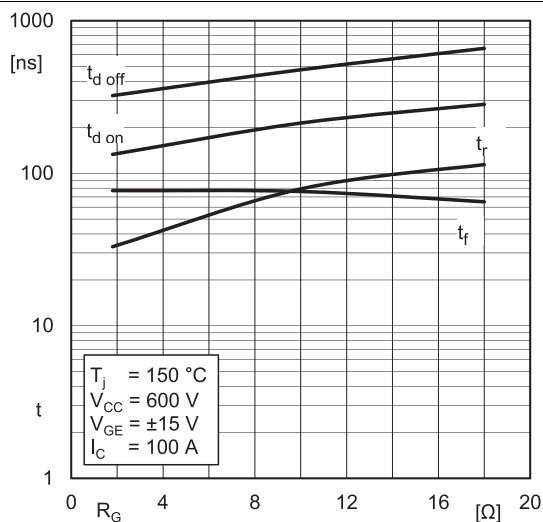


Fig. 8: Typ. switching times = $f(R_G)$

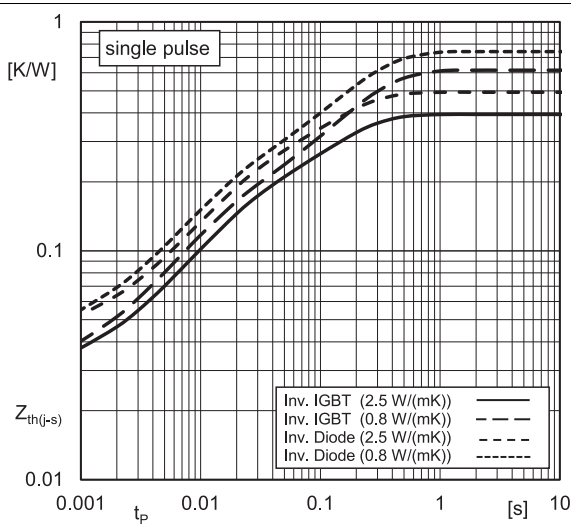


Fig. 9: Typ. transient thermal impedance

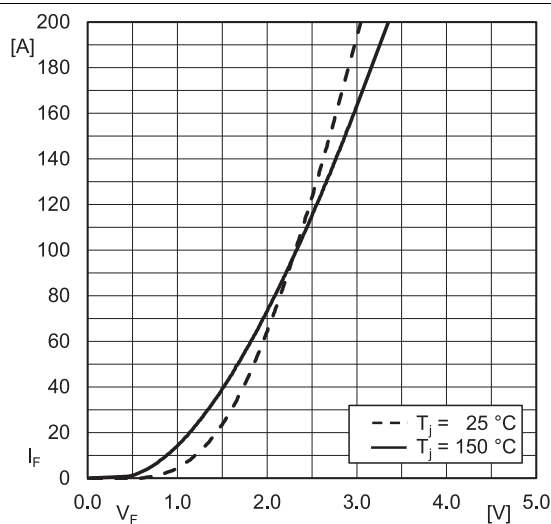


Fig. 10: Typ. Inv. diode forward charact., incl. $R_{CC'} + EE'$

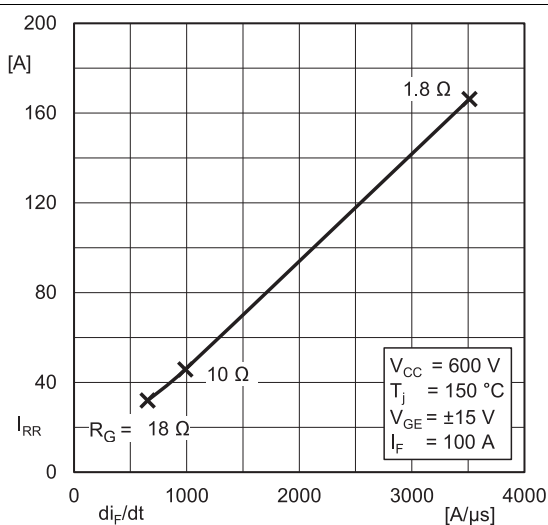


Fig. 11: Typ. Inv. diode peak reverse recovery current

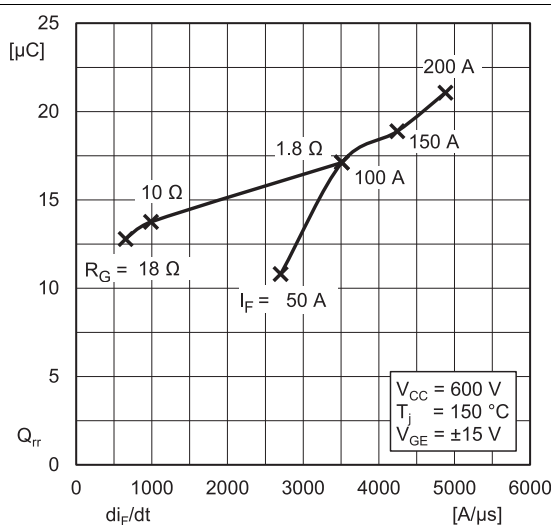


Fig. 12: Typ. Inv. diode reverse recovery charge

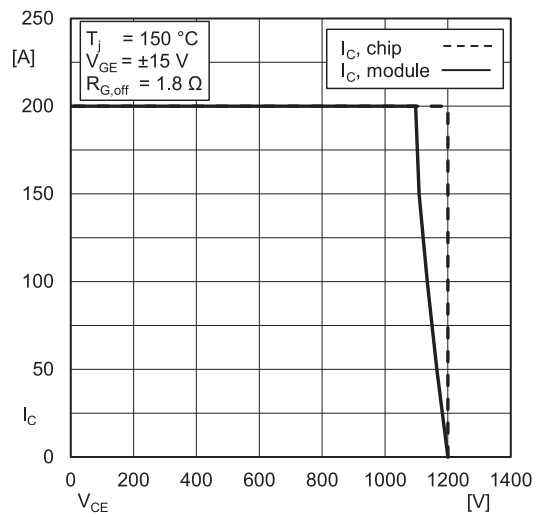
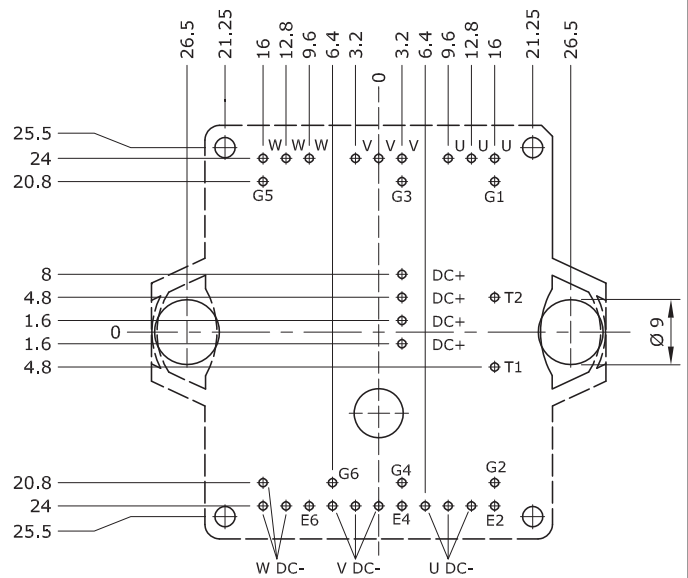
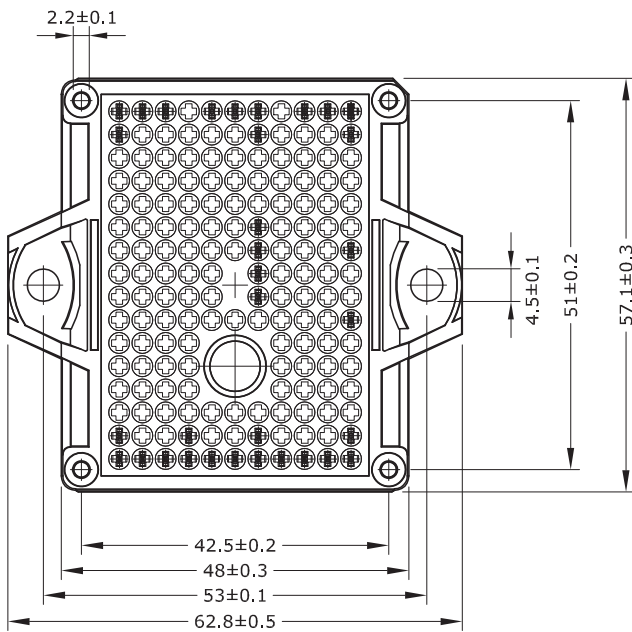
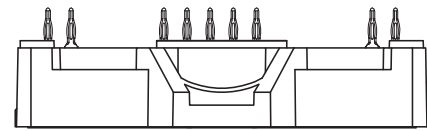
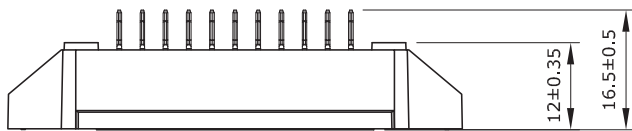
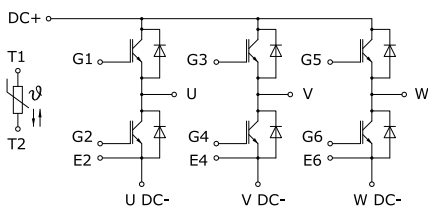


Fig. 13: IGBT Reverse Bias Safe Operating Area (RBSOA)



- Pin-Grid 3.2 mm
- Tolerance of PCB hole pattern $\oplus \oplus \phi 0.1$
- Diameters of drill $\phi 1.15\text{mm}$
- Copper thickness in hole 25 - 50 μm
- Hole specification for contacts:
refer to SEMITOP E1/E2 Mounting Instruction

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This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

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